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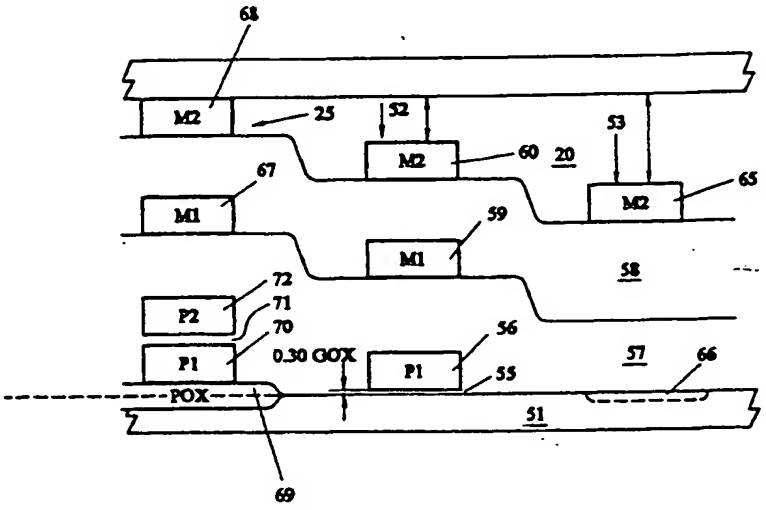
(54) Title: SPACERS FOR CELLS HAVING SPACED OPPOSED SUBSTRATES



(57) Abstract

In an active semiconductor backplane for a liquid crystal spatial light modulator, spacers (25) which are distributed over the backplane extend above an array of electrical and/or electronic elements and comprise at least two layers essentially of the same material and occuring in the same rder as is found in at least one of the electrical or electronic elements, such as an NMOS transist r (52). The latter is formed from a stack of layers on a silicon substrate (51) comprising polysilicon (56), continuous silicon oxide (57) modified t include gate oxide GOX (55), metallic gate electrode (59), continuous silicon oxide (58) and a metallic drain electrode (60) which is coupled to a spaced mirror electrode over the layer (58). Likewise, spacer (25) comprises the layers (57 and 58) with metallic (67, 68) deposited simultaneously with electrodes (59, 60). The foot of layer (57) is differently modified to include field oxide layer (69) and polysilicon layers (70, 72) spaced by thin oxide (71). Spacers (25) are located regularly within the array of transistors (25)/mirrors (65) and also about the array.